MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

2SA1015

Product specification





FEATURES

- High voltage and high current
- Excellent hFE Linearity
- Low niose
- Complementary to 2SC1815

Reference News

PACKAGE OUTLINE		MARKING	
1 2	1. BASE 2. EMITTER 3.COLLECTOR	BA	
SOT-23			

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
Vcво	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
lc	Collector Current -Continuous	150	mA
Pc	Collector Power Dissipation	200	mW
RθJA	Thermal Resistance From Junction To Ambient	625	°C/W
TJ	Junction Temperature	150	℃
T _{stg}	Storage Temperature	-55~+150	$^{\circ}$

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

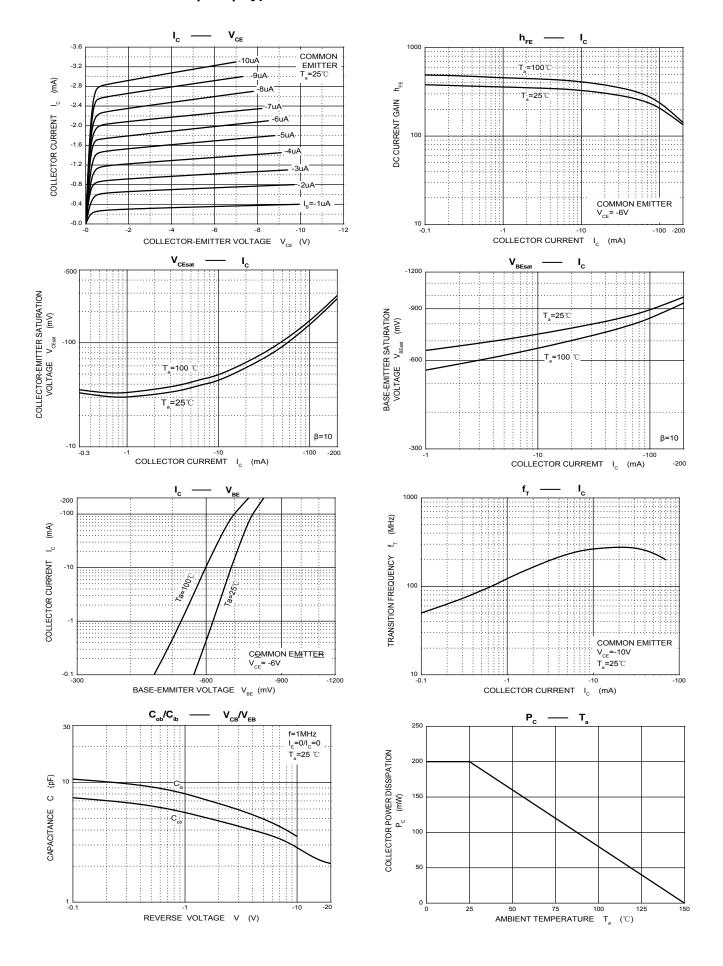
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100uA,I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -0.1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V(BR)EBO	l _E = -100 u A, l _C =0	-5			V
Collector cut-off current	Ісво	V _{CB} =-50V ,I _E =0			-0.1	μA
Collector cut-off current	ICEO	V _{CE} = -50V , I _B =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =- 5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-6V,I _C = -2mA	130		400	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =-100 mA, I _B = -10mA			-0.3	V
Base-emitter saturation voltage	V _{BE} (sat)	Ic=-100 mA, I _B = -10mA			-1.1	V
Transition frequency	f⊤	V _{CE} =-10V,I _C = -1mA f=30MHz	80			MHz

CLASSIFICATION OF hFE

Rank	L	Н	
Range	130-200	200-400	

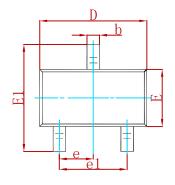


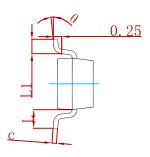
BIPOLAR TRANSISTOR (PNP) Typical Characteristics

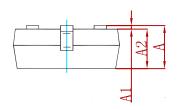




PACKAGE MECHANICAL DATA

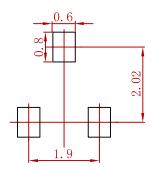






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2SA1015	SOT-23	3000



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